

ABSTRACT

A semiconductor device includes a gate structure including a gate electrode on a substrate. A source/drain pattern is on the substrate and positioned on a side surface of the gate electrode. A source/drain contact is on the source/drain pattern. A first conductive pad is on the source/drain contact. A second conductive pad is on the gate structure. A via plug penetrates the first conductive pad and is connected to the source/drain contact. A gate contact penetrates the second conductive pad and is connected to the gate electrode. A portion of the via plug protrudes from the first conductive pad. A portion of the gate contact protrudes from the second conductive pad. A height from an upper surface of the gate structure to an upper surface of the via plug is equal to a height from the upper surface of the gate structure to an upper surface of the gate contact.

FIG. 2